

MGA-655T6

Low Noise Amplifier with Bypass Mode in Low Profile Package

Description

Avago Technologies' MGA-655T6 is an economical easy-to-use GaAs MMIC Low Noise Amplifier (LNA) with Bypass mode. The Bypass mode enables the LNA to be bypassed during high input signal power and reduce current consumption. Its housed in a low profile 2 x 1.3 x 0.4mm 6-pin Ultra Thin Package.



Lifecycle status: **Active**



Features

- Broadband operation (2.5 – 4)GHz
- Adjustable bias current for gain/IP3 optimization
- Very low noise figure
- Bypass mode using a single pin
- Low current consumption in bypass mode, <100 μ A
- Fully matched to 50 ohm in bypass mode
- High Linearity in LNA and bypass mode
- GaAs E-pHEMT Technology[1]
- Low profile package size: 2.0 x 1.3 x 0.4 mm³
- Excellent uniformity in product specifications

Applications

- Low noise amplifier for Wimax, Wireless Local Loop

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Data Sheet

Description

Avago Technologies' MGA-655T6 is an economical, easy-to-use GaAs MMIC Low Noise Amplifier (LNA) with Bypass mode. The LNA has low noise and high linearity achieved through the use of Avago Technologies' proprietary 0.5 μm GaAs Enhancement-mode pHEMT process. The Bypass mode enables the LNA to be bypassed during high input signal power and reduce current consumption. It is housed in a low profile 2 x 1.3 x 0.4 mm 6-pin Ultra Thin Package. The compact footprint and low profile coupled with low noise, high linearity make the MGA-655T6 an ideal choice as a low noise amplifier for mobile and CPE receivers in the WiMax and WLL (2.5-4) GHz band.

Component Image

2.0 x 1.3 x 0.4 mm³ 6-Lead Ultra Thin Package



Note:

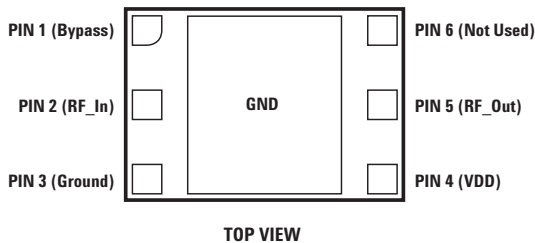
Package marking provides orientation and identification

"5F" = Product Code

"Y" = Year of Manufacture

"M" = Month of Manufacture

Pin Configuration



Features

- Low nominal operating current
- Simple input/output matching network
- Broadband operation (2.5 – 4) GHz
- Adjustable bias current for gain/IP3 optimization
- Very low noise figure
- Bypass mode using a single pin
- Low current consumption in bypass mode, <100 μA
- Fully matched to 50 ohm in bypass mode
- High Linearity in LNA and bypass mode
- GaAs E-pHEMT Technology^[1]
- Low profile package size: 2.0 x 1.3 x 0.4 mm³
- Excellent uniformity in product specifications
- Tape-and-reel packaging option available

Typical Performance

- 3.5 GHz; Vdd = 3 V, Vbypass = 2.7 V (typ.), I_{ds} = 10 mA (typ.)
- 14.7 dB gain
- 1.2 dB noise figure
- +5.5 dBm Input IP3
- -2 dBm input power at 1 dB gain compression
- 4.2 dB insertion loss in bypass mode
- 19 dBm IIP3 in bypass mode (pin = -20 dBm)
- <104 μA current consumption in bypass & shutdown mode

Applications

- Low noise amplifier for Wimax, Wireless Local Loop
- Other ultra low noise applications in the (2.5 – 4) GHz band

Note:

1. Enhancement mode technology employs positive V_{gs}, thereby eliminating the need of negative gate voltage associated with conventional depletion mode devices.



Attention: Observe precautions for handling electrostatic sensitive devices.

ESD Machine Model = 50 V

ESD Human Body Model = 200 V

Refer to Avago Technologies Application Note A004R:

Electrostatic Discharge, Damage and Control.

Absolute Maximum Rating^[1] $T_A = 25^\circ\text{C}$

Symbol	Parameter	Units	Absolute Max.
V_{dd}	Device Voltage, RF Output to Ground	V	4
V_{bypass}	Control Voltage	V	4
$P_{in,max}$	CW RF Input Power	dBm	+14
P_{diss}	Total Power Dissipation ^[3]	mW	66
T_j	Junction Temperature	$^\circ\text{C}$	150
T_{STG}	Storage Temperature	$^\circ\text{C}$	-65 to 150

Thermal Resistance^[2,3]

($V_{dd} = 3.0\text{ V}$, $I_d = 10\text{ mA}$), $\theta_{jc} = 75^\circ\text{C/W}$

Notes:

1. Operation of this device in excess of any of these limits may cause permanent damage.
2. Thermal resistance measured using Infra-Red Measurement Technique.
3. For module substrate temperature, T_{sub} , $>94^\circ\text{C}$ derate the device power at 50 mW per $^\circ\text{C}$ rise in board (module belly) temperature.

Product Consistency Distribution Charts

Process Capability for Gain
LSL=12.8, Nominal=14.7, USL=17

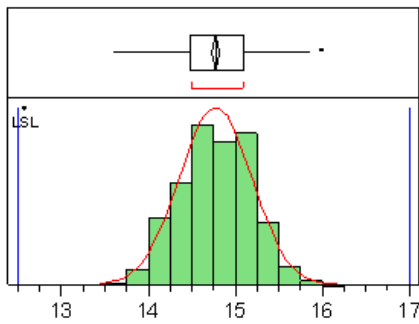


Figure 1. Gain @ 3.5 GHz, V_d 3 V; V_{bypass} 2.7 V

Process Capability for NF
Nominal=1.2, USL=1.6

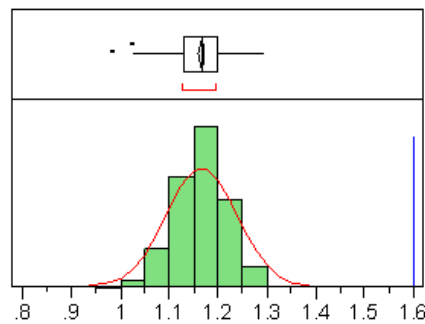


Figure 2. NF @ 3.5 GHz, V_d 3 V; V_{bypass} 2.7 V

Process Capability for I_{ds}
Nominal=10.1, USL=14

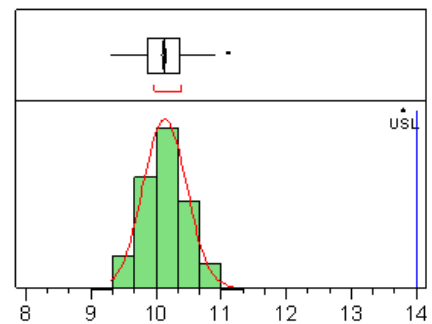


Figure 3. I_{ds} @ 3.5 GHz, V_d 3 V; V_{bypass} 2.7 V

Note:

Distribution data sample size is 500 samples taken from 3 different wafers and 3 different lots. Future wafers allocated to this product may have nominal values anywhere between the upper and lower limits.

Electrical Specifications

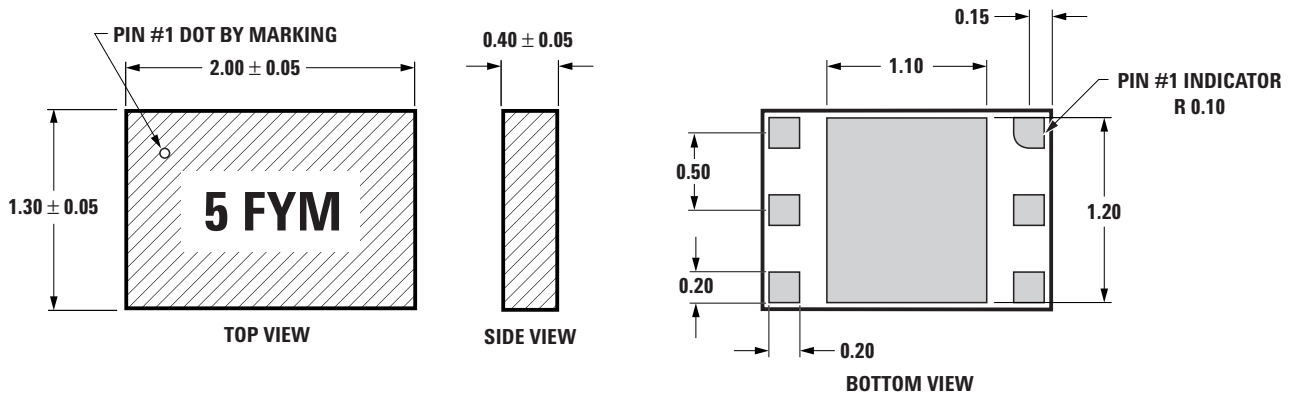
$T_A = 25^\circ\text{C}$, $V_{dd} = 3\text{ V}$, $V_{bypass} = 2.7\text{ V}$, $I_{ds} = 10\text{ mA}$ (typ), RF measurement at 3.5 GHz, measured on demo board (see Fig. 4) unless otherwise specified.

Symbol	Parameter and Test Condition	Units	Min.	Typ.	Max.
Gain	Gain	dB	12.8	14.7	17.0
I_d	Bias Current	mA	-	10	14.0
IIP3 [8]	Input Third Order Intercept Point	dBm	-	+5.5	-
NF [9]	Noise Figure (Typ. $V_{bypass}=2.7\text{V}$)	dB	-	1.2	1.6
OP1dB	Output Power at 1dB Gain Compression	dBm	-	+12	-
S11	Input Return Loss, 50 Ω source	dB	-	-9	-
S22	Output Return Loss, 50 Ω load	dB	-	-13.5	-
S12	Reverse Isolation	dB	-	-24.7	-
$ S_{21} ^2_{\text{BYPASS}}$	Bypass Mode Loss ($V_{bypass} = 0$)	dB	-	4.2	-
IIP3 BYPASS	Bypass Mode IIP3 (tested at -20dBm input Power)	dBm	-	+ 19	-
I_d BYPASS	Bypass Mode current ($V_{bypass} = 0$)	μA	-	100	-

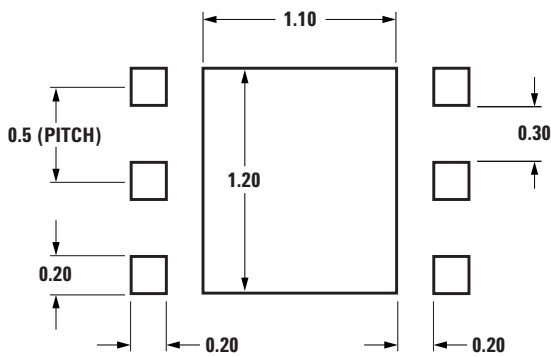
Notes:

1. Measurements at 3.5 GHz obtained using demo board described in Figure 4, with component values on Figure 5.
2. 3.5 GHz IIP3 test condition: $F_{RF1} = 3.50\text{ GHz}$, $F_{RF2} = 3.505\text{ GHz}$ with input power of -20 dBm per tone.
3. Bypass Mode IIP3 test condition: $F_{RF1} = 3.50\text{ GHz}$, $F_{RF2} = 3.505\text{ GHz}$ with input power of -20 dBm per tone.

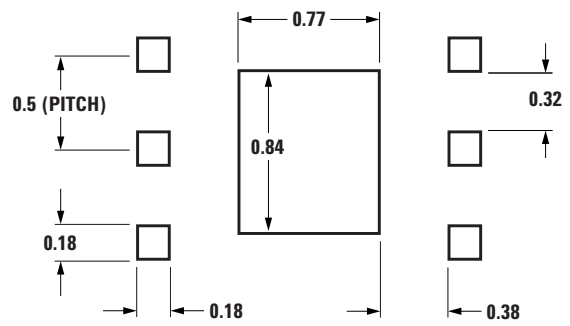
Package Dimensions



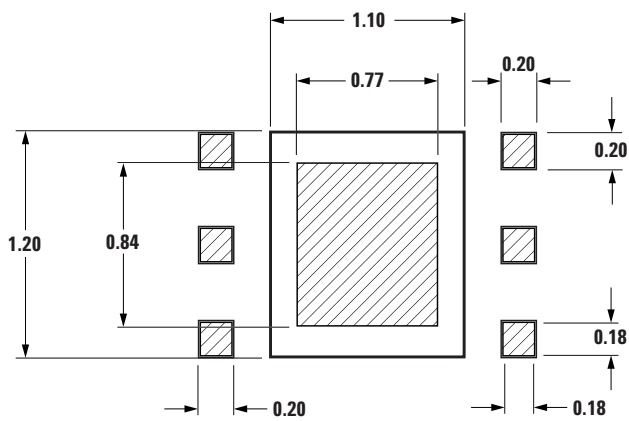
PCB Land Patterns and Stencil Design



PCB Land Pattern (dimensions in mm)

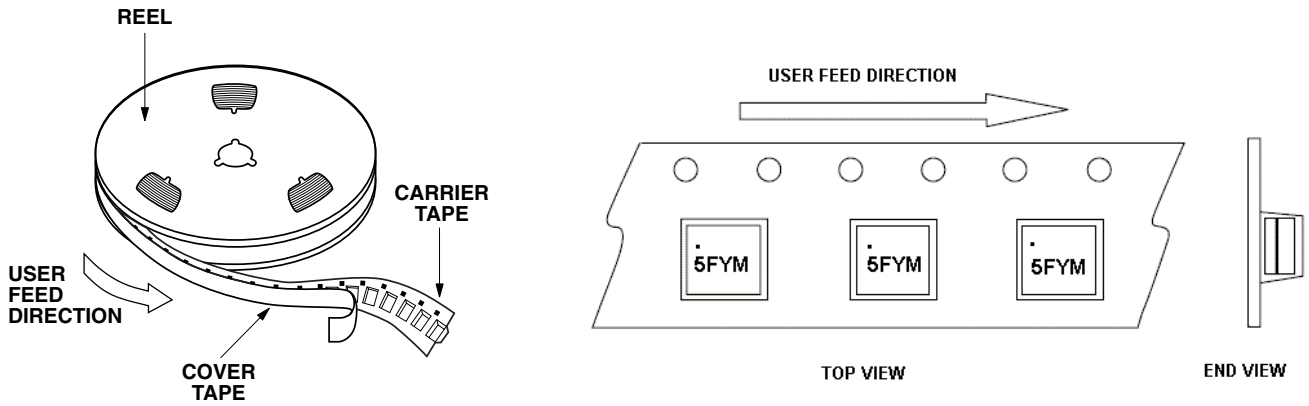


Stencil Outline Drawing (dimensions in mm)

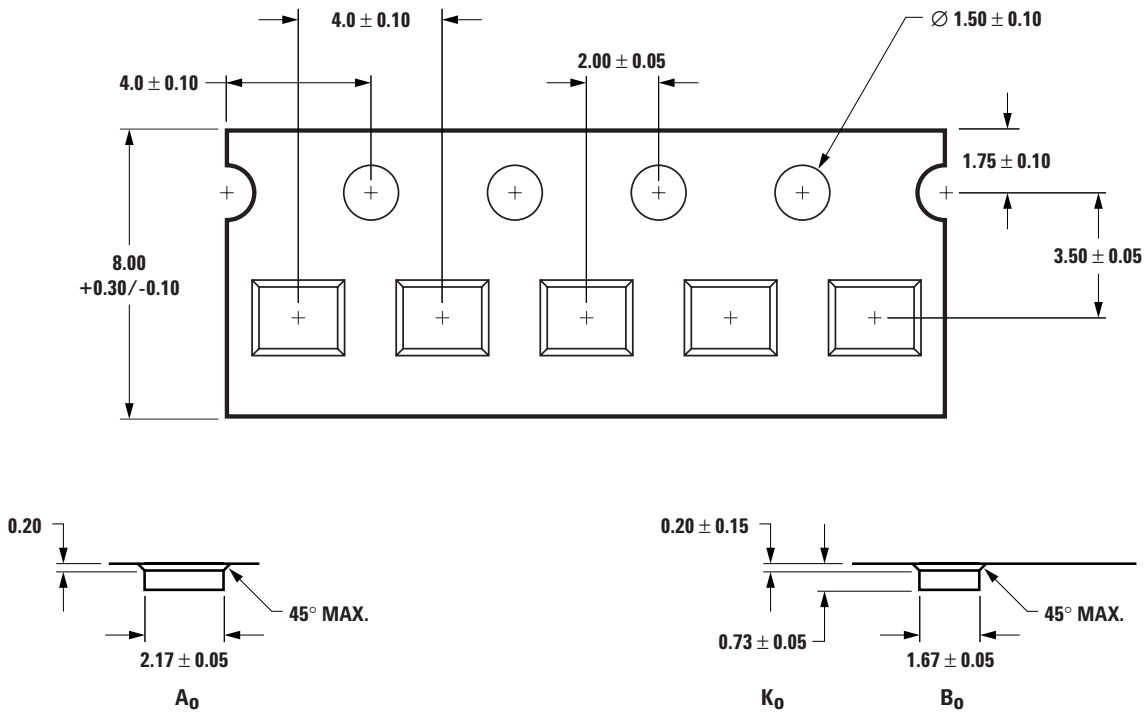


Combined PCB and Stencil Layouts (dimensions in mm)

Device Orientation



Tape Dimensions



Part Number Ordering Information

Part Number	Quantity	Container
MGA-655T6-BLKG	100	Antistatic Bag
MGA-655T6-TR1G	3000	7" Reel
MGA-655T6-TR2G	10000	13" Reel